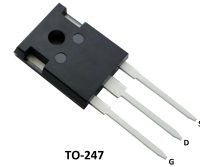
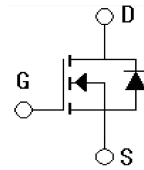


Features

- Very low FOM $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- Easy to use/drive
- RoHS compliant

Applications

- Uninterruptible Power Supply
- Power Factor Correction



Absolute Ratings (T_c=25°C)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	900	V
Drain Current-continuous	I _D , T=25°C T=100°C	30	A
		22	A
Drain Current-pulse (note 1)	I _{DM}	120	A
Gate-Source Voltage	V _{GSS}	±30	V
Single Pulsed Avalanche Energy (note 2)	E _{AS}	280	mJ
Repetitive Avalanche Energy(note 2)	E _{AR}	0.5	mJ
Avalanche Current	I _{AR}	7.5	A
Power Dissipation	PD TC=25°C Derate above 25°C	240	W
		1.92	W/°C
Operating and Storage Temperature Range	T _J , T _{STG}	-55~+150	°C

Electrical Characteristics(T_{CASE}=25°C unless otherwise specified)

Parameter	Symbol	Tests conditions	Min	Typ	Max	Units
Drain-Source Voltage	BV _{DSS}	I _D =250μA, V _{GS} =0V	900	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =900V, V _{GS} =0V	-	-	1	μA
		V _{DS} =900V, T _C =150°C	-	-	100	μA
Gate body leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±30V	-	-	±100	nA

On-Characteristics

Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.5	-	4.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=15V, I_D=20A$	-	170	-	m Ω
Dynamic Characteristics						
Input capacitance	C_{iss}	$V_{DS}=50V, V_{GS}=0V,$ $f=1.0MHz$	-	2840	-	pF
Output capacitance	C_{oss}		-	220	-	pF
Reverse transfer capacitance	C_{rss}		-	16	-	pF

Electrical Characteristics($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Tests conditions	Min	Typ	Max	Units
Switching-Characteristics						
Turn-On delay time	$t_{d(on)}$	$V_{DD}=400V, I_D=30A,$ $R_G=25\Omega$	-	49	-	ns
Turn-On rise time	t_r		-	42	-	ns
Turn-Off delay time	$t_{d(off)}$		-	166	-	ns
Turn-Off rise time	t_f		-	23	-	ns
Total Gate Charge	Q_g	$V_{DS}=720V, I_D=30A,$ $V_{GS}=10V$	-	62	-	nC
Gate-Source charge	Q_{gs}		-	15	-	nC
Gate-Drain charge	Q_{gd}		-	23	-	nC
Drain-Source Diode Characteristics and Maximum Ratings						
Body Diode Forward Current	I_{SD}	$T_C=25^{\circ}C$	-	-	30	A
Body Diode Forward Voltage	V_{SD}	$I_{SD}=30A, V_{GS}=0V$	-	-	1.2	V
Reverse recovery time	t_{rr}	$V_R=400, I_F=30A$ $di_F/dt=100A/\mu s$	-	680	-	ns
Reverse recovery charge	Q_{rr}		-	9	-	μC
Peak Reverse Recovery Current	I_{rrm}		-	24	-	A

Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance, junction to Case	$R_{th(j-C)}$	0.52	$^{\circ}C/W$
Thermal Resistance, junction to Ambient	$R_{th(j-A)}$	62	$^{\circ}C/W$

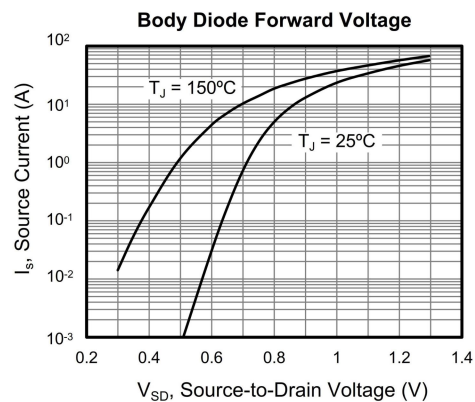
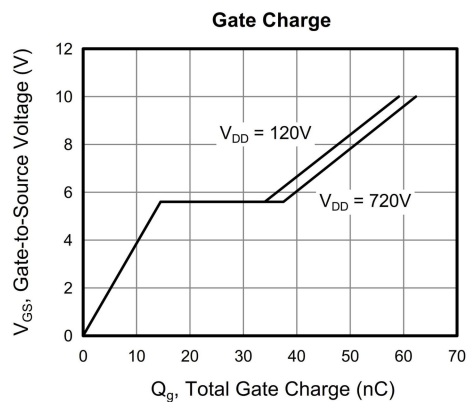
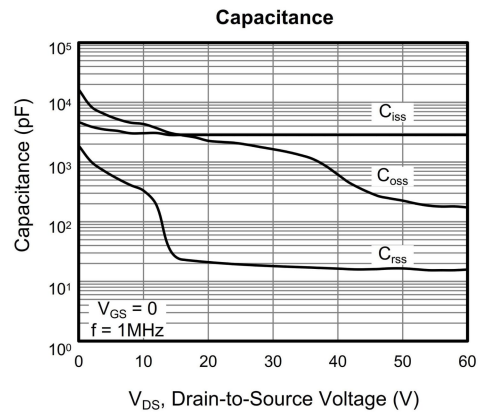
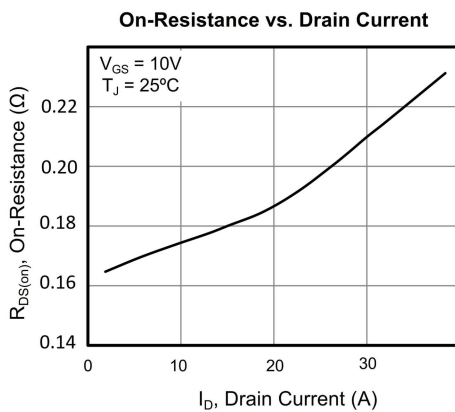
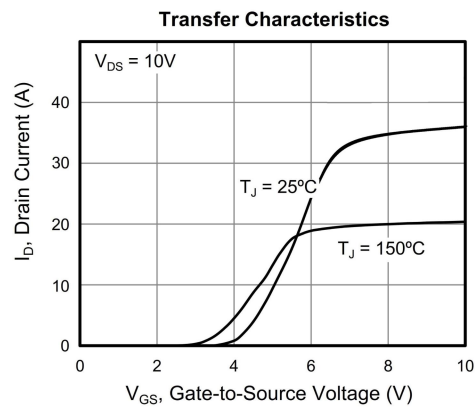
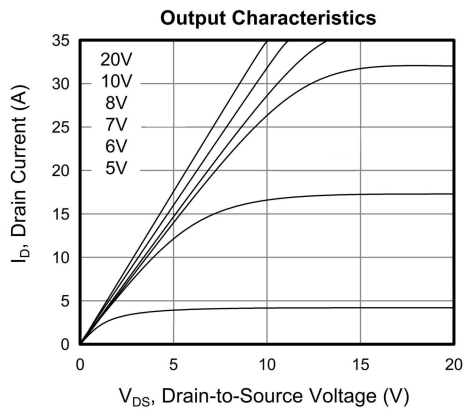
Order Message

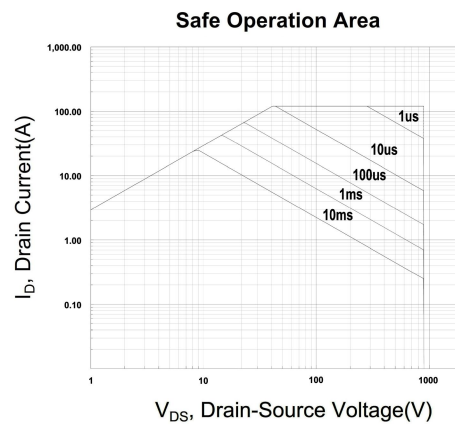
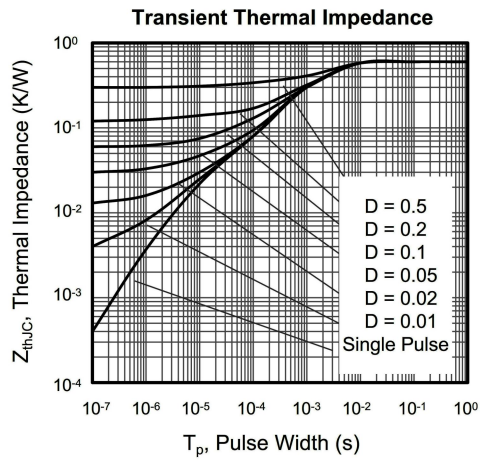
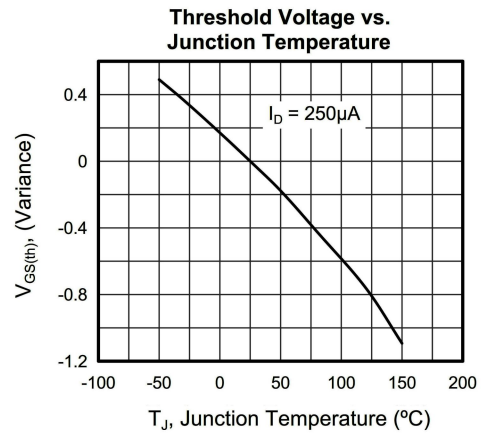
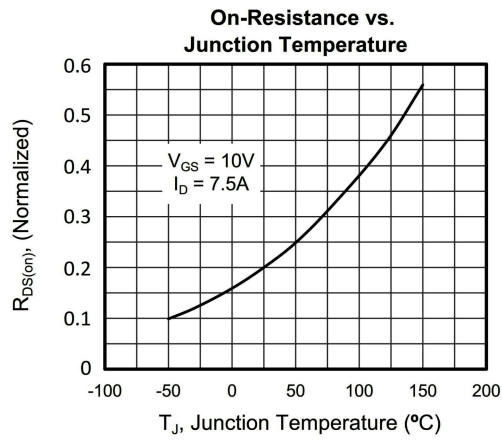
Marking	Package
MS30N90ICE0	TO-263
MS30N90ICC0	TO-247

Notes:

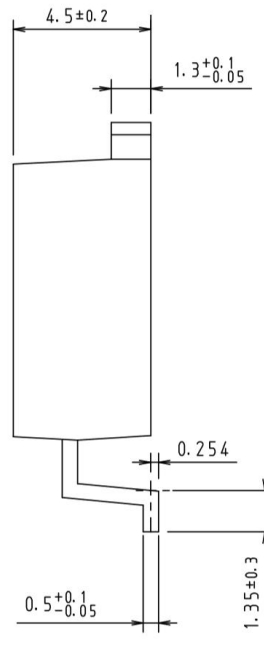
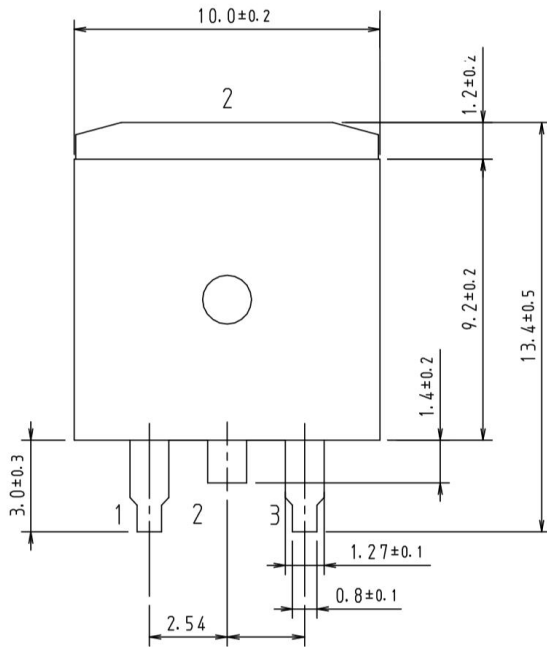
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $I_D = 10A$, $V_{DD} = 50V$, $R_G = 25\Omega$, Starting $T_J = 25^\circ C$
3. Identical low side and high side switch with identical R_G

Typical Characteristics ($T_J = 25^\circ C$, unless otherwise noted)





Package Mechanical DATA



Unit:mm

